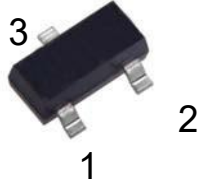



## SOT-23 Plastic-Encapsulate Transistors

 <p><b>MMBTA56 (NPN)</b></p> <p><b>Features:</b></p> <ul style="list-style-type: none"> <li><input type="checkbox"/> High Stability and High Reliability</li> <li><input type="checkbox"/> Power Dissipation of 225mW</li> <li><input type="checkbox"/> Complementary to MMBTA06</li> </ul> <p><b>Marking:2GM</b></p>	<p>SOT-23</p>   <p>1.Base (B) 2. Emitter (E) 3. Collector (C)</p>
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Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

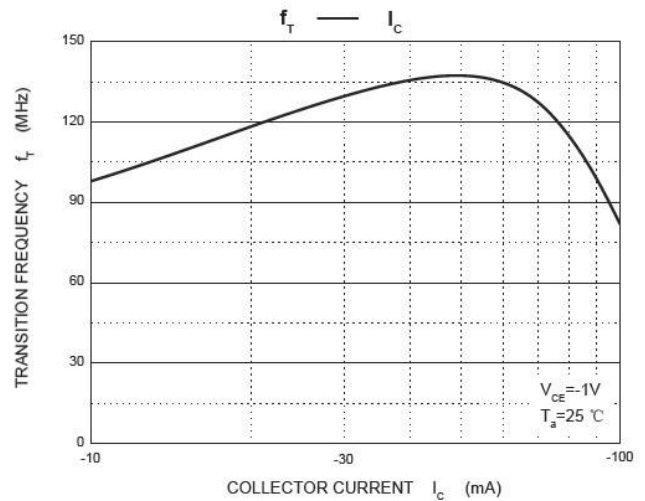
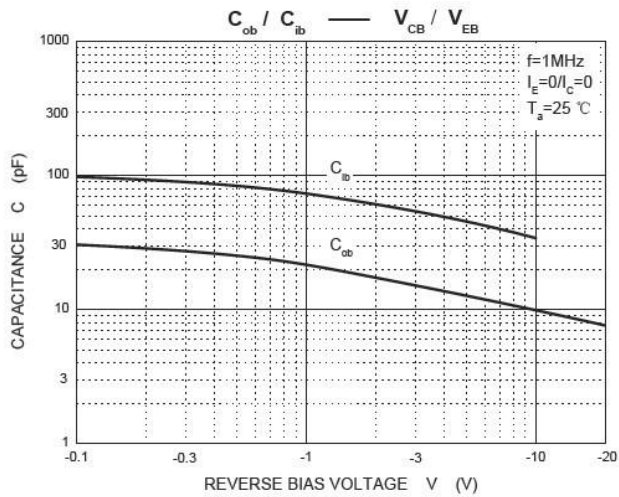
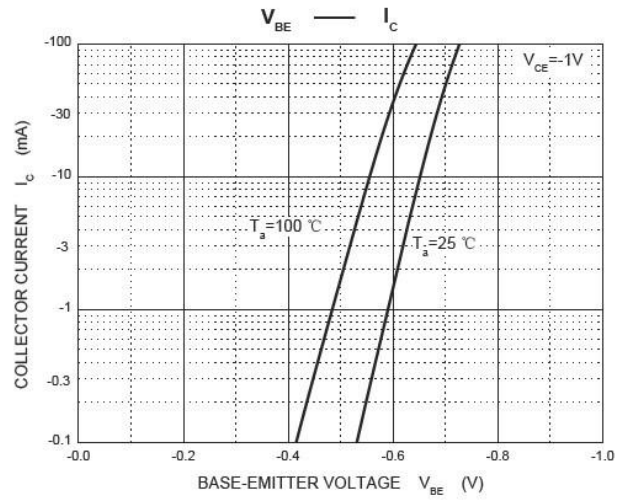
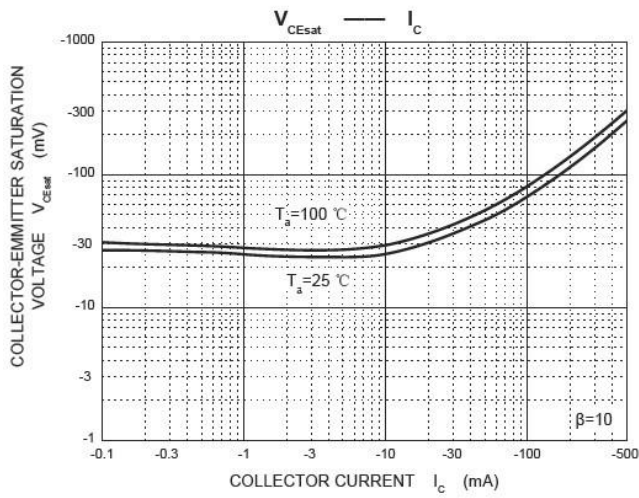
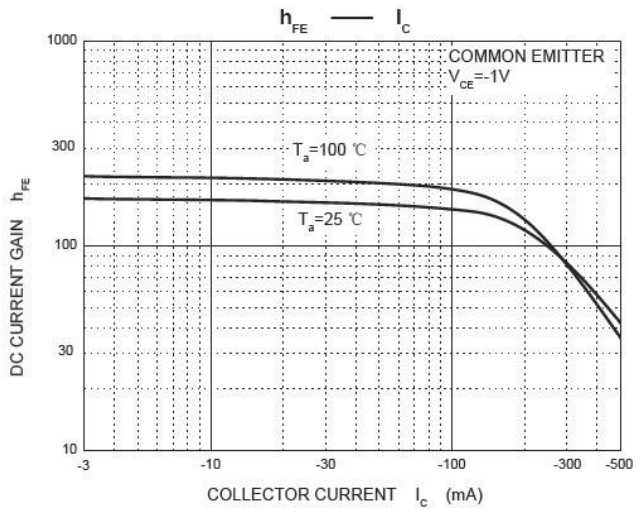
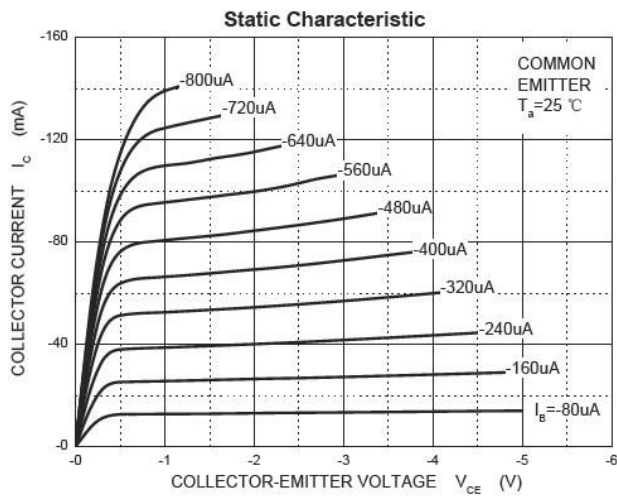
Parameters	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	V
Emitter -Base Voltage	V <sub>EBO</sub>	-4	V
Collector Current-Continuous	I <sub>C</sub>	-500	mA
Collector Power Dissipation	P <sub>C</sub>	225	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55-+150	°C
Thermal resistance From junction to ambient	R <sub>θJA</sub>	555	°C/W

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I <sub>C</sub> =-100uA, I <sub>E</sub> =0	-80		V
Collector-emitter breakdown voltage	V(BR)CEO *	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-80		V
Emitter-base breakdown voltage	V(BR)EBO	I <sub>E</sub> =-100uA, I <sub>C</sub> =0	-4		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-80V, I <sub>E</sub> =0		-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0		-100	nA
Collector cut-off current	I <sub>CE0</sub>	V <sub>CE</sub> =-60V, I <sub>B</sub> =0		-1.0	uA
DC current gain	h <sub>FE</sub> (1) *	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	100	400	
	h <sub>FE</sub> (2) *	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	100		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-0.25	V
Base -emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA		-1.20	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA, f=100MHz	50		MHz

\*Pulse test: pulse width ≤ 300us, duty cycle ≤ 2.0%

Typical Characteristics



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